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Percentage error in measurement of real part of complex permittivity

Percentage error in measurement of real part of complex permeability

Percentage of match efficiency of the conductor-backed coplanar waveguide structure

Real part of the complex permittivity ($\varepsilon_r'$) of LDPE and Co$_{1-x}$Ni$_x$Fe$_2$O$_4$ - LDPE ($x = 0, 0.2, 0.4, 0.6, 0.8$ and $1.0$) composite with (a) 2% volume fractions and (b) 4% volume fractions

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Yee’s mesh

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The reflection at the interface of two media

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